

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	7713	257/620.ccls. 257/690.ccls. 257/771.ccls. 257/779.ccls. 257/e21.602.ccls. 257/e23.061.ccls. 438/113.ccls. 438/460.ccls. 438/462.ccls.	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT	OR	OFF	2007/05/21 10:51
L2	747	257/620.ccls.	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT	OR	OFF	2007/05/21 12:21
L3	5364	1 and ((wafer substrate semiconductor integrated ic circuit) with (scrib\$ divid\$6 section\$6 saw\$6 cut\$6 separat\$6))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT	OR	ON	2007/05/21 12:24
L4	3940	1 and (((wafer substrate semiconductor integrated ic circuit) with (scrib\$ divid\$6 section\$6 saw\$6 cut\$6 separat\$6)) same (metal\$8 wir\$6 trace line aluminum copper al cu))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT	OR	ON	2007/05/21 12:27
L5	677	1 and (((wafer substrate semiconductor integrated ic circuit) with (scrib\$ divid\$6 section\$6 saw\$6 cut\$6 separat\$6)) same (metal\$8 wir\$6 trace line aluminum copper al cu) same (trench groov\$6))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT	OR	ON	2007/05/21 12:32
L6	340	1 and ((wafer substrate semiconductor integrated ic circuit) same (scrib\$ divid\$6 section\$6 saw\$6 cut\$6 separat\$6) same (metal\$8 wir\$6 trace line aluminum copper al cu) same (trench groov\$6) same (protect\$6 passivat\$6 insulat\$6 dielectric))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT	OR	ON	2007/05/21 12:42
L7	5499	(wafer substrate semiconductor integrated ic circuit) same (scrib\$ divid\$6 section\$6 saw\$6 cut\$6 separat\$6) same (metal\$8 wir\$6 trace line aluminum copper al cu) same (trench groov\$6) same (protect\$6 passivat\$6 insulat\$6 dielectric) same (etch\$6 remov\$6)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT	OR	ON	2007/05/21 12:38

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L8	351	(wafer substrate semiconductor integrated ic circuit) with (scrib\$ divid\$6 section\$6 saw\$6 cut\$6 separat\$6) with (metal\$8 wir\$6 trace line aluminum copper al cu) with (trench groov\$6) with (protect\$6 passivat\$6 insulat\$6 dielectric) with (etch\$6 remov\$6)	US-PGPUB; USPAT	OR	ON	2007/05/21 14:27
L9	3450	(wafer substrate semiconductor integrated ic circuit) and (scrib\$ divid\$6 section\$6 saw\$6 cut\$6 separat\$6) and (metal\$8 wir\$6 trace line aluminum copper al cu) and (trench groov\$6) and (protect\$6 passivat\$6 insulat\$6 dielectric) and (etch\$6 remov\$6)	FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/21 12:40
L10	1803	(wafer substrate semiconductor integrated ic circuit) and (scrib\$ divid\$6 section\$6 saw\$6 cut\$6 separat\$6) and ((metal\$8 wir\$6 trace line aluminum copper al cu) same (trench groov\$6) same (protect\$6 passivat\$6 insulat\$6 dielectric) same (etch\$6 remov\$6))	FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/21 12:40
L11	819	(wafer substrate semiconductor integrated ic circuit) same (scrib\$ divid\$6 section\$6 saw\$6 cut\$6 separat\$6) same (metal\$8 wir\$6 trace line aluminum copper al cu) same (trench groov\$6) same (protect\$6 passivat\$6 insulat\$6 dielectric) same (etch\$6 remov\$6)	FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/21 12:41
L12	200	(wafer substrate semiconductor integrated ic circuit) same (scrib\$ divid\$6 section\$6 saw\$6 cut\$6 separat\$6) same ((metal\$8 wir\$6 trace line aluminum copper al cu) with (trench groov\$6) with (protect\$6 passivat\$6 insulat\$6 dielectric) with (etch\$6 remov\$6))	FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/21 15:40
S1	6	"20020047210".pn. "5606198".pn. "20040121562".pn. "6354909".pn. "5461008".pn. "6454190".pn.	US-PGPUB; USPAT	OR	OFF	2007/05/02 16:06
S2	10	jp-2001223288-\$.did. jp-2002198463-\$.did. jp-2002329852-\$.did. jp-2000077646-\$.did. jp-2003347476-\$.did.	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT	OR	OFF	2007/05/21 10:29